

[SCOPE OF CLAIMS]

1. A semiconductor device characterized by comprising a first film and a second film which are sequentially laminated over a substrate, wherein

5 the first film and the second film each has at least one layer of an insulating layer, a conductive layer, and a semiconductor layer, and

 a face on which the first film and the second film are in contact with each other is made of the conductive layer and at least has the same pattern.

10 2. A semiconductor device according to Claim 1 characterized in that the first film and the second film have at least one of a thin film transistor, a capacitor means, a resistor means, a memory element, a thin film diode, and a photoelectric conversion element.

15 3. A semiconductor device according to Claim 1 characterized in that the first film and the second film have a display portion including a plurality of pixels arranged in a matrix.

 4. A semiconductor device according to Claim 3 characterized in that an EL
20 element or liquid crystal is used for the display portion.

 5. A semiconductor device according to Claim 1, the substrate may have a flat surface or a curved surface.

25 6. A method for manufacturing a semiconductor device characterized by comprising the steps of:

 forming a first film in which a first insulating layer, a first conductive layer, and a first semiconductor layer are formed over a first substrate;

 forming a second film having a second insulating layer, a second conductive
30 layer having at least the same pattern as the first conductive layer, and a second

semiconductor layer over a second substrate;

fixing the first film to a third substrate after peeling the first film off the first substrate; and

laminating the second film over the first film fixed to the third substrate after
5 peeling the second film off the second substrate, wherein

the first film and the second film are connected by contact of the same patterns in the step of laminating.

7. A method for manufacturing a semiconductor device according to Claim 6
10 characterized in that the first conductive layer and the second conductive layer each have at least the same pattern on a face on which the first film and the second film are in contact with each other.

8. A method for manufacturing a semiconductor device according to Claim 6
15 characterized in that a peel layer is formed between the first substrate and the first film.

9. A method for manufacturing a semiconductor device according to Claim 6
characterized in that a step of removing the peel layer is provided between the step of peeling the first film off the first substrate and the step of fixing the first film to the third
20 substrate.

10. A method for manufacturing a semiconductor device according to Claim 6
6 characterized in that a peel layer is formed between the second substrate and the second film.

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11. A method for manufacturing a semiconductor device according to Claim 6 characterized in that a step of removing the peel layer is provided between the step of peeling the second film off the second substrate and the step of laminating the second film over the first film.

12. A method for manufacturing a semiconductor device according to Claim 6 characterized in that the third substrate has a flat surface or a curved surface.

5 13. A method for manufacturing a semiconductor device characterized by comprising the steps of:

forming a first film in which a first insulating layer, a first conductive layer, and a first semiconductor layer are formed over a first substrate;

forming a second film having a second insulating layer, a second conductive layer having at least the same pattern as the first conductive layer, and a second semiconductor layer over a second substrate;

10 peeling the first film off the first substrate by fixing a third substrate to the first film;

fixing the peeled first film to a fourth substrate;

15 peeling the second film off the second substrate by fixing the second film to a fifth substrate; and

laminating the peeled second film over the first film fixed to the fourth substrate, wherein

the first film and the second film are connected by contact of the same patterns with each other in the step of laminating.

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14. A method for manufacturing a semiconductor device according to Claim 13 characterized in that the first conductive layer and the second conductive layer may each at least have the same pattern on a face on which the first film and the second film are in contact with each other.

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15. A method for manufacturing a semiconductor device according to Claim 13 characterized in that a peel layer is formed between the first substrate and the first film.

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16. A method for manufacturing a semiconductor device according to Claim

15 characterized in that a step of removing the peel layer is provided between the step of peeling the first film off the first substrate and the step of fixing the first film to the fourth substrate.

5 17. A method for manufacturing a semiconductor device according to Claim 13 characterized in that a peel layer is formed between the second substrate and the second film.

10 18. A method for manufacturing a semiconductor device according to Claim 17 characterized in that a step of removing the peel layer is provided between the step of peeling the second film off the second substrate and the step of laminating the second film over the first film.

15 19. A method for manufacturing a semiconductor device according to Claim 13 characterized in that the fourth substrate has a flat surface or a curved surface.